

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently amended) A semiconductor device comprising:
a semiconductor chip;
a stud bump provided on an electrode of said semiconductor chip; and
an adhesive layer provided on a surface of said semiconductor chip on which said electrode is formed; and
an interposer bonded to said adhesive layer, wherein said adhesive layer comprises a thermocompressive adhesive,
wherein said adhesive layer comprises an adhesive surface facing away from said semiconductor chip, and
wherein said stud bump projects from said adhesive surface of said adhesive layer.

Claim 2. (Canceled).

Claim 3. (Previously presented) A semiconductor device comprising:
a semiconductor chip;
an adhesive layer provided on a surface of said semiconductor chip on which an electrode is formed;
a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer; and
an interposer adhered to said surface of said adhesive layer through a cured flux and electrically connected to said bump,
wherein said adhesive layer comprises an adhesive surface facing away from said

semiconductor chip.

Claim 4. (Currently amended) The semiconductor device according to claim 1 2,
wherein said interposer is provided with a device hole.

Claim 5. (Previously presented) A semiconductor device comprising:
a semiconductor chip;
an adhesive layer formed on a surface of said semiconductor chip on which an electrode is formed;
a bump provided on said electrode of said semiconductor chip and projecting from a surface of said adhesive layer;
a wiring pattern adhered to said surface of said adhesive layer and partially bonded to said bump; and
an insulating and covering layer for insulating and covering said wiring pattern and selectively opening to form an external connecting portion,
wherein said adhesive layer comprises an adhesive surface facing away from said semiconductor chip.

Claim 6. (Previously presented) A semiconductor device comprising:
a semiconductor chip;
an adhesive layer provided on a surface of said semiconductor chip on which an electrode is formed;
a bump provided on said electrode of said semiconductor chip and exposed at a

surface of said adhesive layer;

a wiring pattern adhered to said surface of said adhesive layer through a cured flux and partially bonded to said bump; and

an insulating and covering layer for insulating and covering said wiring pattern and selectively opening to form an external connecting portion,

wherein said adhesive layer comprises an adhesive surface facing away from said semiconductor chip.

Claim 7. (Previously presented) A semiconductor apparatus comprising:

two or more semiconductor devices, each of said devices comprising:

a semiconductor chip;

an adhesive layer provided on a surface of said semiconductor chip on which an electrode is formed; and

a bump provided on said electrode of said semiconductor chip and projecting from a surface of said adhesive layer,

wherein part of a surface of one of said semiconductor devices on which said adhesive layer is provided is adhered to part or all of a surface of another one of said semiconductor devices on which said adhesive layer is provided and said one and said another one of said semiconductor devices are electrically connected to each other with said bumps at the adhesion surface, and

wherein said adhesive layer comprises an adhesive surface facing away from said semiconductor chip.

Claim 8. (Previously presented) A semiconductor apparatus comprising:

two or more stacked semiconductor devices, each of said devices comprising:

a semiconductor chip having electrodes formed on the front and back;

an adhesive layer provided on the front or back of said semiconductor chip;

and

a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer,

wherein one of said semiconductor devices is adhered to an underlaying one of said semiconductor devices through said adhesive layer and the electrodes thereof are connected to each other through said bump.

Claims 9 - 24. (Cancelled).

Claim 25. (Original) A semiconductor device comprising:

a semiconductor chip;

an adhesive layer provided on a surface of said semiconductor chip on which an electrode is formed;

a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer;

a tape substrate; and

an interposer,

wherein said semiconductor chip is adhered to the front of said tape substrate with said adhesive layer, said semiconductor chip is electrically connected to said tape substrate

with said bump, and said interposer is connected to the back of said tape substrate for allowing electrical conduction.

Claims 26- 30. (Cancelled).

Claim 31. (Currently amended) A semiconductor device comprising:
a semiconductor chip;
a stud bump provided on an electrode of said semiconductor chip; and
an adhesive layer provided on a surface of said semiconductor chip on which said
electrode is formed,
wherein said adhesive layer comprises an adhesive surface facing away from said
semiconductor chip,
wherein said stud bump projects from said adhesive surface of said adhesive layer.
A semiconductor device according to claim 1, and
wherein said adhesive layer comprises a thermoplastic resin having a thickness of 50
μm.